

MN74HC244/MN74HC244S

Octal TRI-STATE Buffers

■ Outline

The MN74HC244/MN74HC244S consists of high speed non-inverting buffers having 3-state outputs.

Because of the large current outputs, these buffers assure high speed operation even when driving a large capacity bus line. They have inputs $1\bar{G}$ and $2\bar{G}$ to enable the outputs when the level is "L", and the respective four buffers can be independently controlled.

Owing to the silicon gate CMOS process, these buffers have realized low power consumption and high noise immunity equivalent to those of a standard CMOS and the operation speed as high as of an LS TTL, and can directly drive fifteen LS TTL inputs.

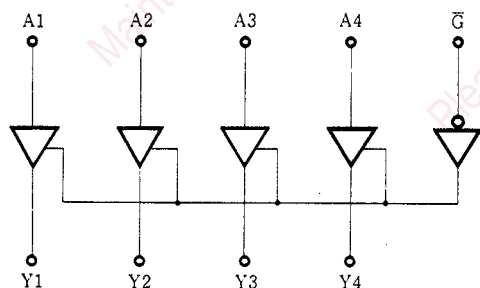
To protect the input and output against electrostatic breakdown, a resistor and a diode are used for the V_{CC} and the GND. The pin configuration and the function are the same those of the standard 54LS/74LS logic family.

■ Truth Table

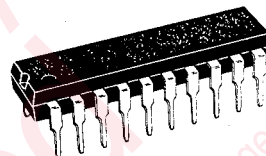
Input		Output	Input		Output
$1\bar{G}$	1A	1Y	$2\bar{G}$	2A	2Y
L	L	L	L	L	L
L	H	H	L	H	H
H	L	Hi-Z	H	L	Hi-Z
H	H	Hi-Z	H	H	Hi-Z

Note) Hiz : High impedance

■ Logic Diagram



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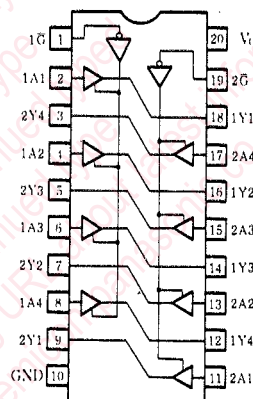
20-pin plastic DIL package

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20-pin PANAFLAT package (SO-20D)

Pin Configuration



■ Absolute Maximum Ratings

Item			Symbol	Rating	Unit
Supply voltage			V_{CC}	$-0.5 \sim +7.0$	V
Input output voltage			V_I, V_O	$-0.5 \sim V_{CC} + 0.5$	V
Input protective diode current			I_{IK}	± 20	mA
Output parasitic diode current			I_{OK}	± 20	mA
Output current			I_O	± 35	mA
Supply current			I_{CC}, I_{GND}	± 70	mA
Storage temperature			T_{stg}	$-65 \sim +150$	°C
Power dissipation	MN74HC244	$T_a = -40 \sim +60^\circ\text{C}$	P_D	400	mW
		$T_a = +60 \sim +85^\circ\text{C}$		Decrease to 200mW at the rate of 8mW/°C	
	MN74HC244S	$T_a = -40 \sim +60^\circ\text{C}$	P_D	275	mW
		$T_a = +60 \sim +85^\circ\text{C}$		Decrease to 200mW at the rate of 3.8mW/°C	

■ Recommended Operating Conditions

Item		Symbol	$V_{CC}(\text{V})$	Rating	Unit
Operating power supply voltage		V_{CC}		1.4~6.0	V
Input output voltage		V_I, V_O		0~ V_{CC}	V
Operating temperature		T_A		$-40 \sim +85$	°C
Input rise, fall time		t_r, t_f	2.0	0~1000	ns
			4.5	0~500	ns
			6.0	0~400	ns

■ DC Characteristics ($GND=0V$)

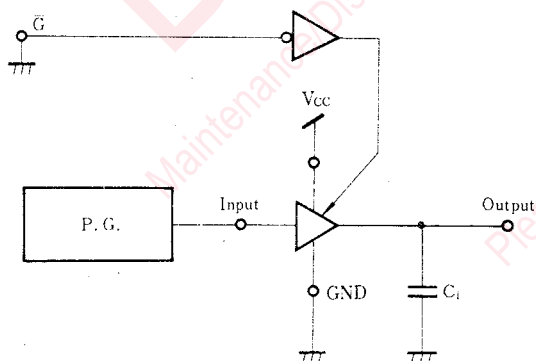
Item	Symbol	V _{CC} (V)	Test Condition			Temperature					Unit
			V _I	V _O	Unit	Ta=25°C			Ta=-40~+85°C		
						min.	typ.	max.	min.	max.	
Input voltage high level	V _{IH}	2.0				1.5			1.5		V
		4.5				3.15			3.15		
		6.0				4.2			4.2		
Input voltage low level	V _{IL}	2.0						0.3		0.3	V
		4.5						0.9		0.9	
		6.0						1.2		1.2	
Output voltage high level	V _{OH}	2.0		-20.0	μA	1.9	2.0		1.9		V
		4.5	V _{IH}	-20.0	μA	4.4	4.5		4.4		
		6.0	or	-20.0	μA	5.9	6.0		5.9		
		4.5	V _{IL}	-6.0	mA	3.92			3.84		
		6.0		-7.8	mA	5.48			5.34		
Output voltage low level	V _{OL}	2.0		20.0	μA		0.0	0.1		0.1	V
		4.5	V _{IH}	20.0	μA		0.0	0.1		0.1	
		6.0	or	20.0	μA		0.0	0.1		0.1	
		4.5	V _{IL}	6.0	mA			0.26		0.33	
		6.0		7.8	mA			0.26		0.33	
Input leakage current	I _I	6.0	V _I =V _{CC} or GND					±0.1		±1.0	μA
3-state output OFF leakage current	I _{OZ}	6.0	V _I =V _{IH} or V _{IL} V _O =V _{CC} or GND					±0.5		±5.0	μA
Static supply current	I _{CC}	6.0	V _I =V _{CC} or GND, I _O =0					8.0		80.0	μA

■ AC Characteristics (GND=0V, Input transition time $\leq 6\text{ns}$, $C_L=50\text{pF}$)

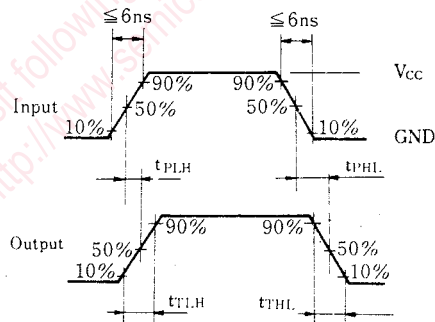
Item	Symbol	V _{CC} (V)	Test Condition	Temperature					Unit
				Ta=25°C			Ta=-40~+85°C		
				min.	typ.	max.	min.	max.	
Output rise time	t _{TLH}	2.0			18	75		95	ns
		4.5			9	15		19	
		6.0			6	13		16	
Output fall time	t _{THL}	2.0			14	75		95	ns
		4.5			5	15		19	
		6.0			4	13		16	
Propagation time (L→H)	t _{PLH}	2.0			15	75		95	ns
		4.5			8	15		19	
		6.0			7	13		16	
Propagation time (H→L)	t _{PHL}	2.0			15	75		95	ns
		4.5			7	15		19	
		6.0			6	13		16	
3-state propagation time (H→Z)	t _{PHZ}	2.0	R _L =1kΩ		20	125		155	ns
		4.5			14	25		31	
		6.0			13	21		26	
3-state propagation time (L→Z)	t _{PLZ}	2.0	R _L =1kΩ		23	125		155	ns
		4.5			14	25		31	
		6.0			13	21		26	
3-state propagation time (Z→H)	t _{PZH}	2.0	R _L =1kΩ		22	100		125	ns
		4.5			10	20		25	
		6.0			8	17		21	
3-state propagation time (Z→L)	t _{PZL}	2.0	R _L =1kΩ		27	125		155	ns
		4.5			11	25		31	
		6.0			9	21		26	

● Switching time measuring circuit and waveforms
(1) t_{TLH} , t_{THL} , t_{PLH} , t_{PHL}

1. Measuring circuit



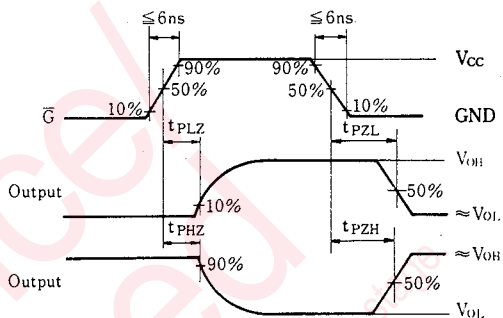
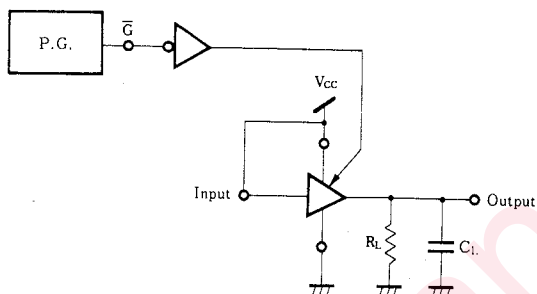
2. Switching waveforms



(2) t_{PHZ} , t_{PZH}

1. Measuring circuit

2. Switching waveforms

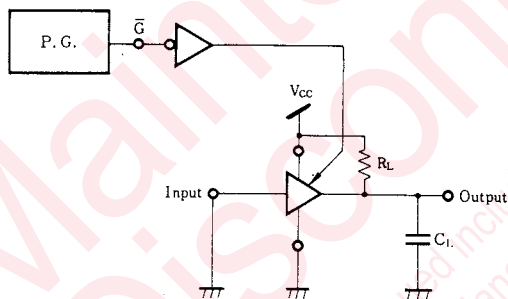


(3) t_{PLZ} , t_{PZL}

1. Measuring circuit

2. Switching waveforms

See above (2) 2 for waveforms.



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